In the Claims:

1. (withdrawn)
2. (withdrawn)
3. (withdrawn)
4. (withdrawn)
5. (withdrawn)
6. (withdrawn)
7. (cancelled)
8. (cancelled)
9. (cancelled)
10. (cancelled)
11. (cancelled)
12. (currently amended) A method of endpoint detection in plasma etching of a target layer of material, comprising the actions of:
measuring voltage across a plasma system by measuring a voltage ~~difference~~ across an element that is external to said plasma system;
detecting a change of the voltage prior to the completion of the etching of the target layer of material; and
stopping etch when said voltage ~~decreases~~ change exceeds a predetermined amount within a predetermined time.
13. (original) The method of Claim 12, wherein said element is a resistor.
14. (previously amended) The method of Claim 12, wherein said predetermined amount is a voltage change of not less than 5% from a reference voltage and said predetermined time is not less than 3 seconds.
15. (cancelled)
16. (cancelled)
17. (cancelled)
18. (cancelled)
19. (new) The method of Claim 12, wherein the element is part of an impedance matching network.